

L Number	Hits	Search Text	DB	Time stamp
-	1602	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3	USPAT	2004/10/14 15:43
-	553	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) same etch\$3 same (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3	USPAT	2004/10/14 16:14
-	9	6441492.pn. or 6368484.pn. or 6339258.pn. or 6333560.pn. or 5865984.pn. or 5486282.pn. or 6375693.pn. or 6503834.pn. or 6731004.pn.	USPAT	2004/10/14 15:47
-	1252	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3 and etch\$3 same (copper or "Cu")	USPAT	2004/10/14 16:15
-	283	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3 and etch\$3 near (copper or "Cu")	USPAT	2004/10/14 16:15
-	4121	damas\$4 and (copper or "Cu")	USPAT	2004/10/14 20:49
-	2209	damas\$4 and (copper or "Cu") and cap\$4	USPAT	2004/10/14 20:51
-	0	etching with electrochemicaletching with (copper or "Cu")	USPAT	2004/10/14 20:52
-	0	electrochemicaletching with (copper or "Cu")	USPAT	2004/10/14 20:52
-	23	electroetching with (copper or "Cu")	USPAT	2004/10/14 20:56
-	590	chemical near etching with (copper or "Cu")	USPAT	2004/10/14 20:57
-	25337	(electroetching with (copper or "Cu")) an d16	USPAT	2004/10/14 20:56
-	1	(electroetching with (copper or "Cu")) and (chemical near etching with (copper or "Cu"))	USPAT	2004/10/14 20:56
-	3	chemical near etching with (copper or "Cu") with recess	USPAT	2004/10/14 21:01
-	13	chemical near etching with (copper or "Cu") and recess with (copper or "Cu")	USPAT	2004/10/14 21:43
-	36	"5380546"	USPAT	2004/10/14 21:16
-	185	etching with (copper or "Cu") and recess with (copper or "Cu")	USPAT	2004/10/14 21:43
-	20	etching with (copper or "Cu") and recess with (copper or "Cu") and seed\$3 and electroless	USPAT	2004/10/14 21:51
-	0	recess with (copper or "Cu") and seeding with (copper or "Cu") and electroless with cap\$4	USPAT	2004/10/14 21:52
-	123	nozzle with electroplat\$3	USPAT	2004/10/14 21:53
-	6	nozzle with electroplat\$3 and (copper with "Cu")	USPAT	2004/10/14 21:53
-	35	nozzle with electroplat\$3 with (metal or alloy)	USPAT	2004/10/14 21:54
-	6	nozzle with electroplat\$3 with diameter	USPAT	2004/10/14 21:56
-	0	nozzle with electroplat\$3 with diameter and damascene	USPAT	2004/10/14 21:56
-	0	nozzle with electroplat\$3 with diameter and (plug or interconnect)	USPAT	2004/10/14 22:02
-	542	438/654	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/14 22:14
-	1710	438/653	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/14 22:41

-	2040	438/687	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 12:28
-	124	(seed\$3 or seeding or dop\$3 or impurit\$3) with (copper or "Cu") and electroless near plating with cap\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 12:30
-	32	((seed\$3 or seeding or dop\$3 or impurit\$3) with (copper or "Cu") and electroless near plating with cap\$4) and (remov\$3 or etch\$3) with barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 12:30
-	4878	257/758	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 14:57